

PWG15N65TFD

IGBT 650V, 1.55V, 15A



重庆平伟实业股份有限公司

Features

- 650V Trench field-stop technology
- Low conduction and switching losses
- Positive temperature coefficient of forward voltage
- Qualified according to JEDEC criteria



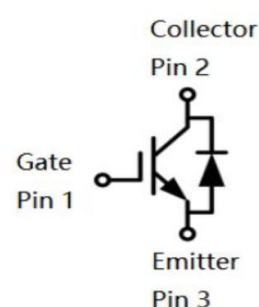
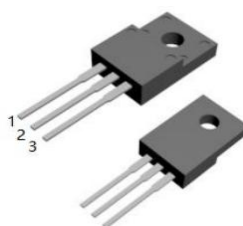
Applications

- Solar Inverter, UPS, Welder, Telecom, ESS

Product Summary

V_{CE}	650V
$V_{CE(sat)}$	1.55V
I_C	15A

TO-220TF-3L



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
PWG15N65TFD	PWG15N65TFD	TO-220TF-3L	Tube	N/A	N/A	50pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	650	V
Collector current $T_C=25^{\circ}\text{C}$ $T_C=100^{\circ}\text{C}$	I_C	30 15	A
Diode forward current $T_C=25^{\circ}\text{C}$ $T_C=100^{\circ}\text{C}$	I_F	30 15	A
Pulsed collector current, t_p limited by T_{vjmax}	$I_{C\ pulse}$	60	A
Gate-emitter voltage	V_{GE}	± 30	V
Power dissipation $T_C=25^{\circ}\text{C}$	P_{tot}	35	W
Operating junction and storage temperature	T_{vj}, T_{stg}	-55...+150	$^{\circ}\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	$^{\circ}\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction-case.(IGBT)	R_{thJC}	-	-	3.59	°C/W	-
Thermal resistance, junction-case.(Diode)	R_{thJC}	-	-	6.75	°C/W	-
Thermal resistance, junction-ambient	R_{thJA}	-	-	72	°C/W	-

Electrical Characteristic (at $T_{vj}=25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Collector-emitter breakdown voltage	BV_{CES}	650	-	-	V	$V_{GE}=0V, I_C=250\mu A$
Gate threshold voltage	$V_{GE(th)}$	5.0	-	6.5	V	$V_{CE}=V_{GE}, I_C=1mA$
Zero gate voltage collector current	I_{CES}	-	-	4 1000	μA	$V_{CE}=650V, V_{GE}=0V$ $T_{vj}=25^{\circ}\text{C}$ $T_{vj}=150^{\circ}\text{C}$
Gate-emitter leakage current	I_{GES}	-	-	± 200	nA	$V_{GE}=\pm 30V, V_{CE}=0V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	1.55 1.83	2.00 -	V	$V_{GE}=15V, I_C=15A$ $T_{vj}=25^{\circ}\text{C}$ $T_{vj}=150^{\circ}\text{C}$

Dynamic Characteristic

Input capacitance	C_{ies}	-	898	-	pF	$V_{GE}=0V, V_{CE}=25V,$ $f=1MHz$
Output capacitance	C_{oes}	-	42	-		
Reverse transfer capacitance	C_{res}	-	10	-		
Gate total charge	Q_G	-	37	-	nC	$V_{CE}=520V, I_C=15A$ $V_{GE}=15V$
Gate-collector charge	Q_{gc}	-	17	-		
Gate-emitter charge	Q_{ge}	-	10	-		

Switching Characteristic, Inductive Load

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

IGBT Characteristic, at $T_{vj}=25^{\circ}\text{C}$

Turn-on delay time	$t_{d(on)}$	-	17	-	ns	$I_C=15A,$ $V_{CE}=400V,$ $V_{GE}=15V,$ $R_G=10\Omega,$ $T_{vj}=25^{\circ}C,$ Inductive load
Rise time	t_r	-	22	-		
Turn-off delay time	$t_{d(off)}$	-	84	-		
Fall time	t_f	-	111	-		
Turn-on energy	E_{on}	-	0.24	-	mJ	
Turn-off energy	E_{off}	-	0.38	-		
Total switching energy	E_{ts}	-	0.62	-		

Switching Characteristic, Inductive Load

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

IGBT Characteristic, at $T_{vj}=150^{\circ}\text{C}$

Turn-on delay time	$t_{d(on)}$	-	28	-	ns	I _C =15A, V _{CC} =400V, V _{GE} =15V, R _G =10Ω, T _{vj} =150°C, Inductive load
Rise time	t _r	-	36	-		
Turn-off delay time	$t_{d(off)}$	-	125	-		
Fall time	t _f	-	157	-		
Turn-on energy	E _{on}	-	0.40	-	mJ	
Turn-off energy	E _{off}	-	0.85	-		
Total switching energy	E _{ts}	-	1.25	-		

ELECTRICAL CHARACTERISTICS OF THE DIODE, at $T_{vj}=25^{\circ}\text{C}$

Diode forward voltage	V_F	-	1.77	2.10	V	$I_F=15\text{A}$
Reverse recovery time	T_{rr}	-	88	106	ns	$I_F=15\text{A},$ $dI_F/dt=200\text{A/us}$
Reverse recovery charge	Q_{rr}	-	166	-	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

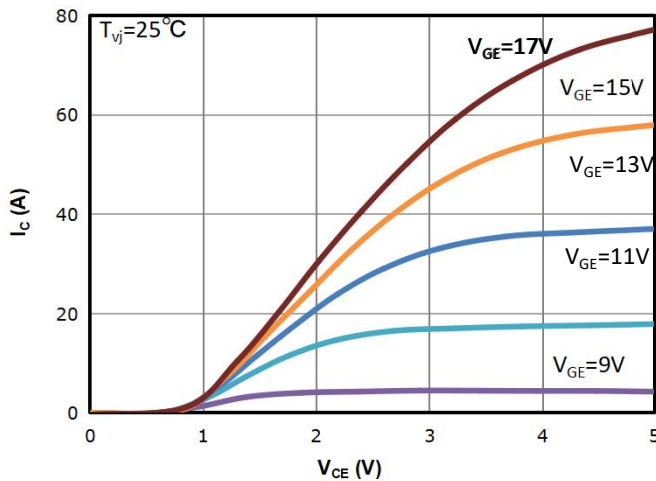


Fig 2: Output Characteristics

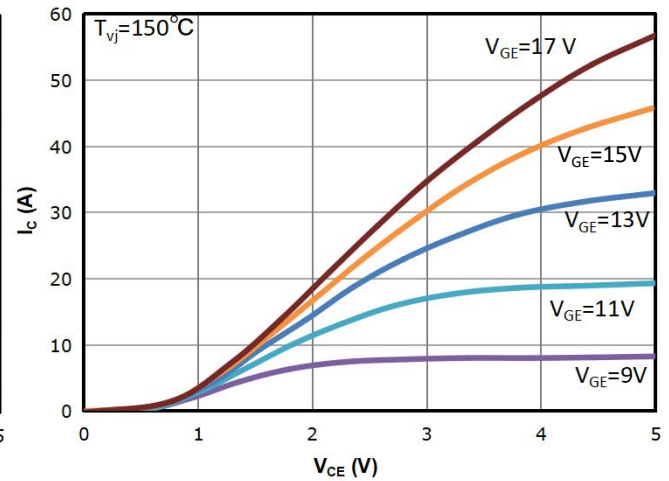


Fig 3: Transfer Characteristics

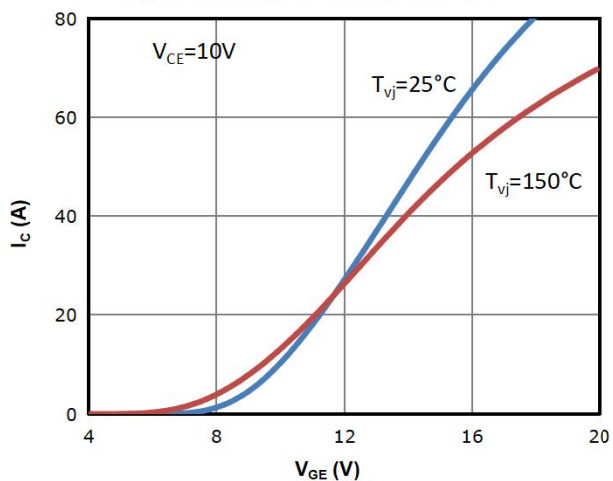


Fig 4: Typical Saturation Voltage Characteristic

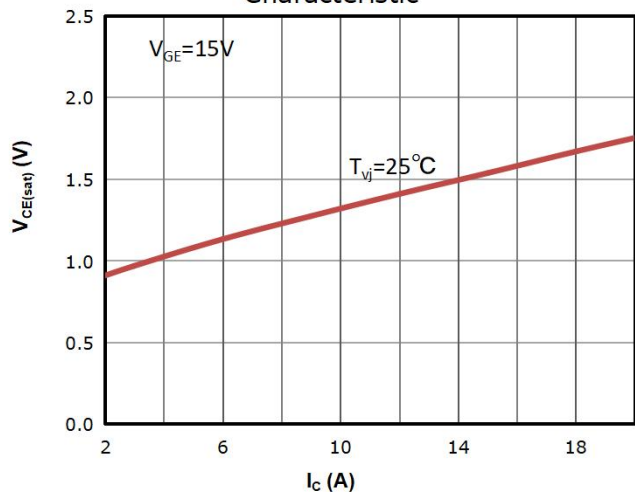


Fig 5: $V_{ce(sat)}$ vs. Gate Voltage

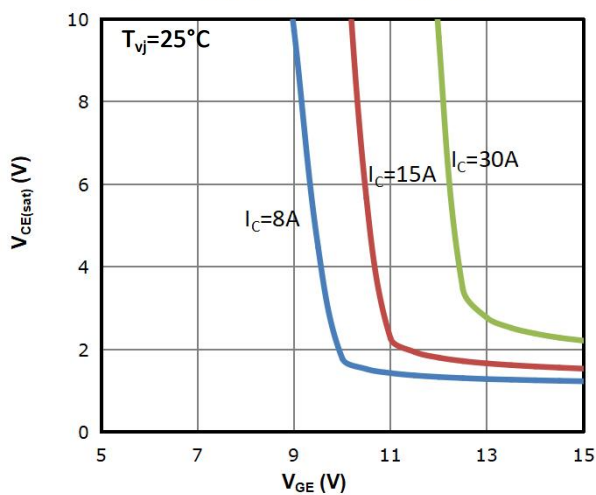


Fig 6: $V_{ce(sat)}$ vs. Temperature

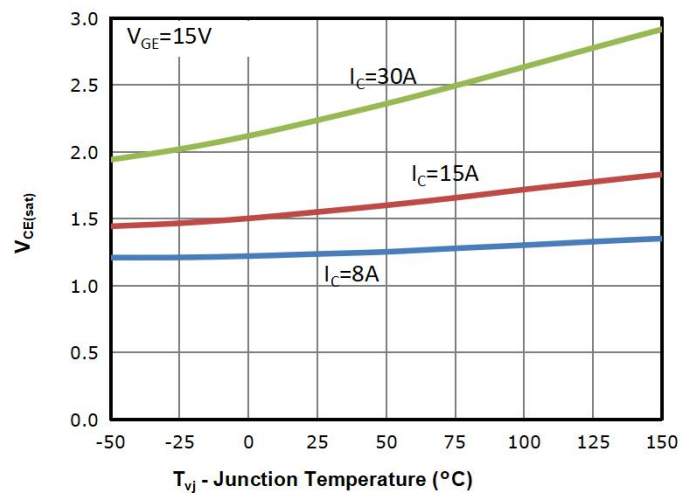


Fig 7: $V_{GE(th)}$ vs. Temperature

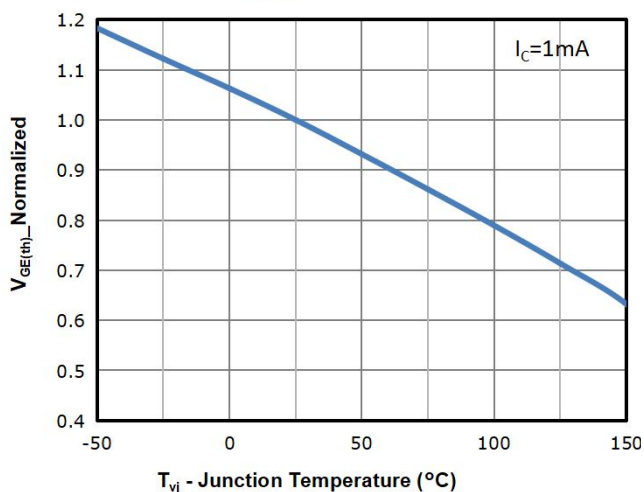


Fig 8: BV_{ces} vs. Temperature

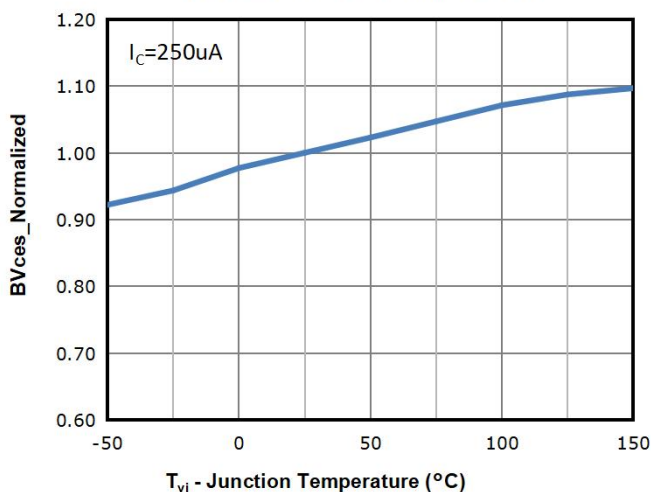


Fig 9: Forward characteristic

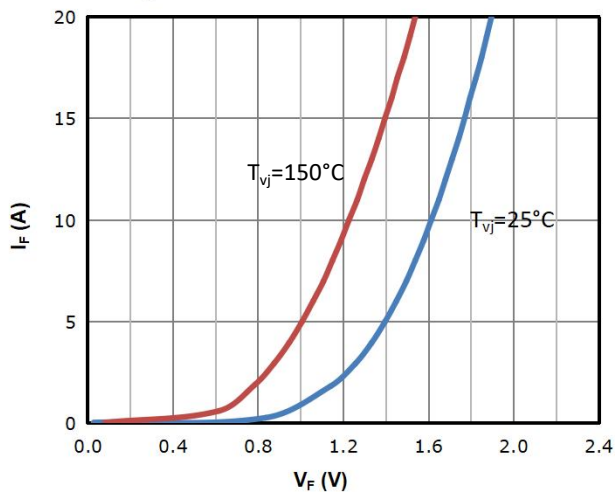


Fig 10: V_F vs. Temperature

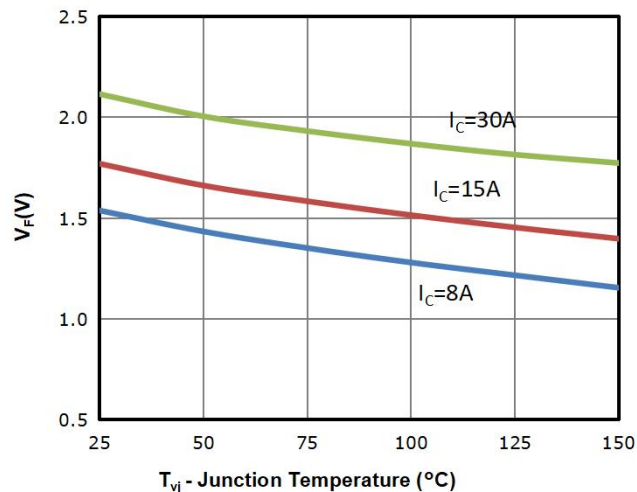


Fig 11: Capacitance Characteristics

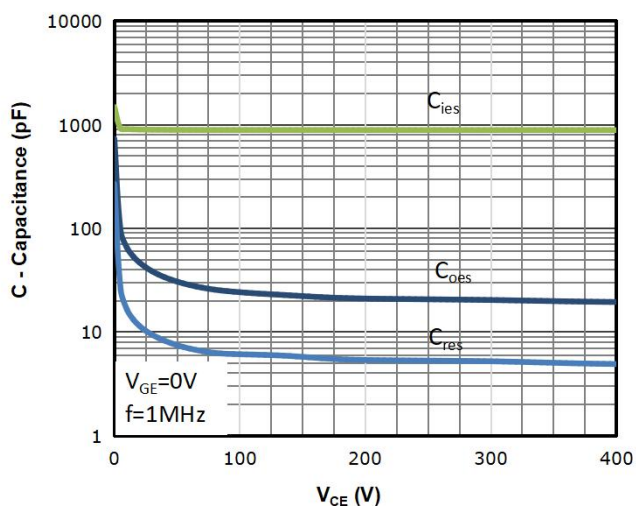


Fig 12: Gate Charge Characteristics

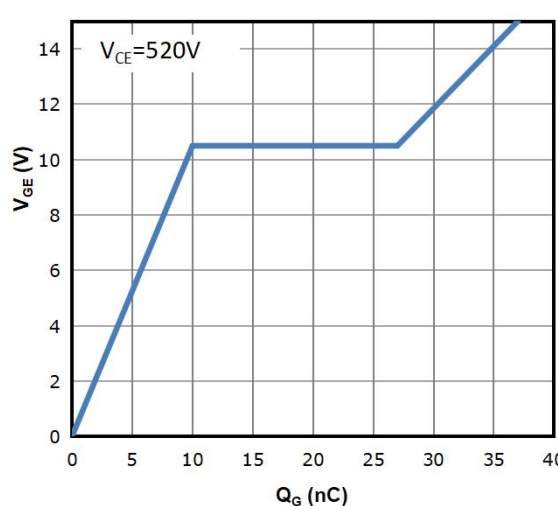


Fig 13: Typical Switching Time vs. R_G

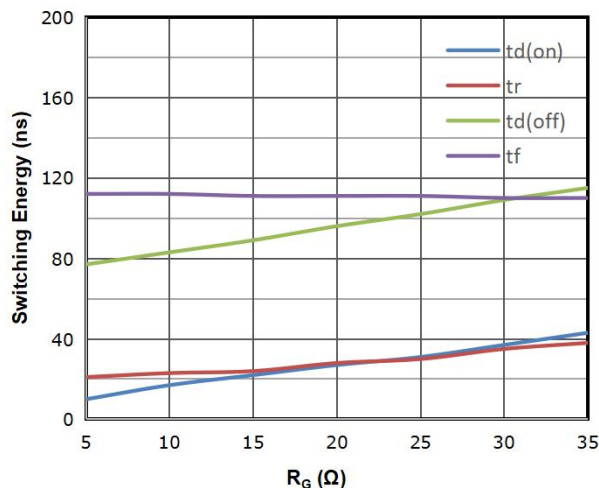


Fig 14: Typical Switching Energy vs. R_G

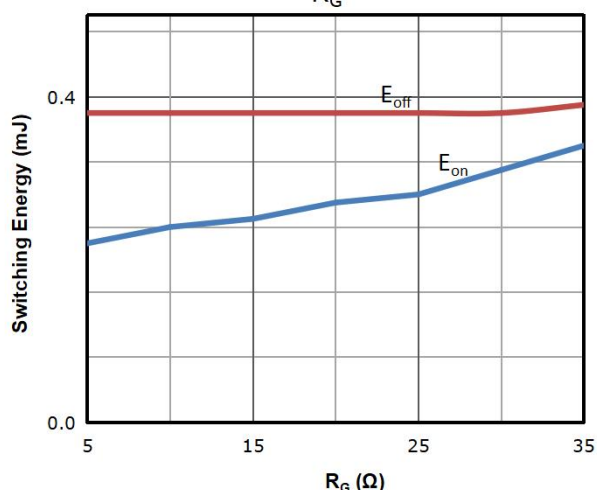


Fig 15: IGBT Max. Transient Thermal Impedance

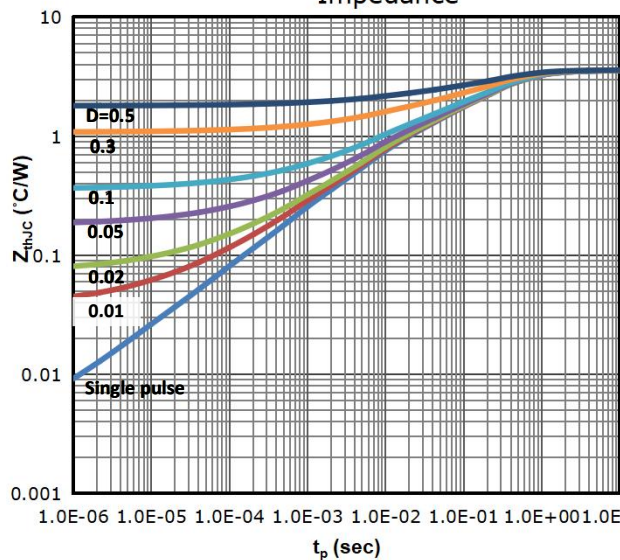


Fig 16: Diode Max. Transient Thermal Impedance

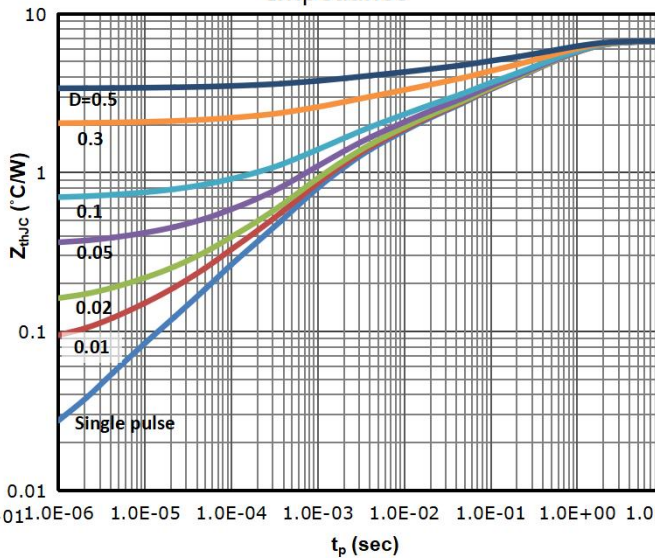
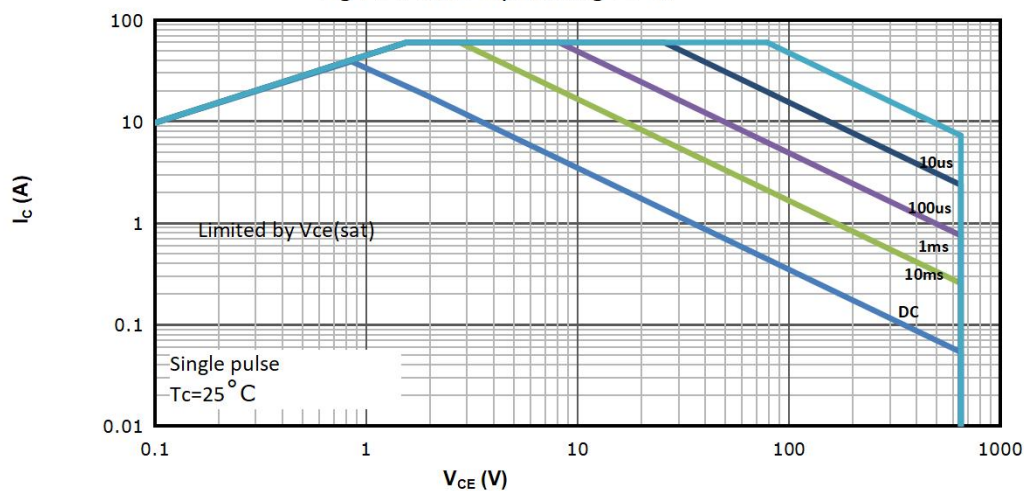
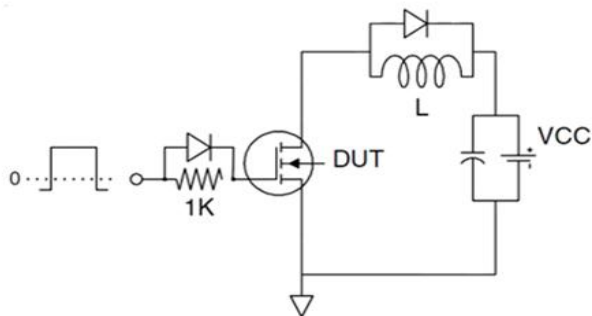


Fig 17: Safe Operating Area

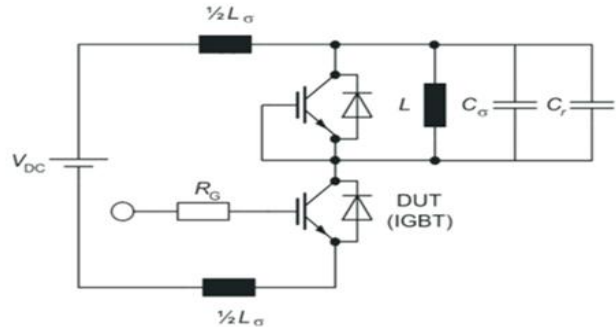


Test Circuit

1) Gate Charge Test Circuit

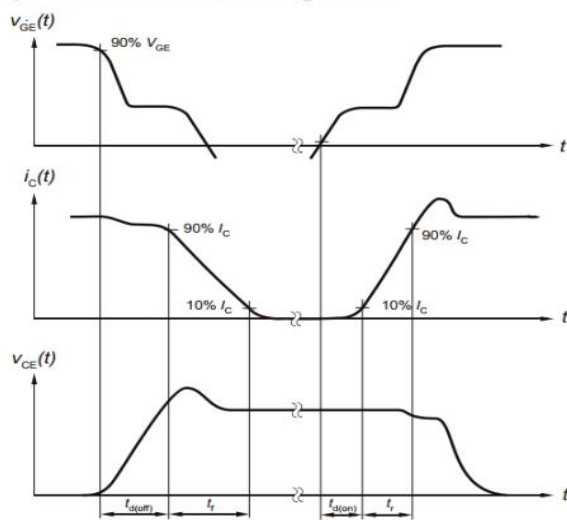


2) Switch Time Test Circuit

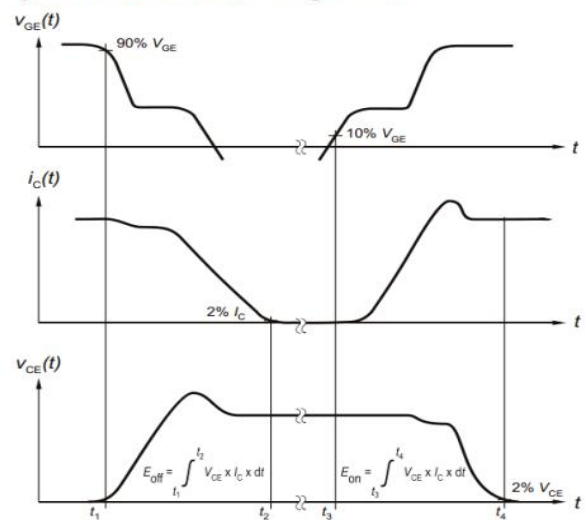


Switching characteristics

1) Definition of switching times



2) Definition of switching losses



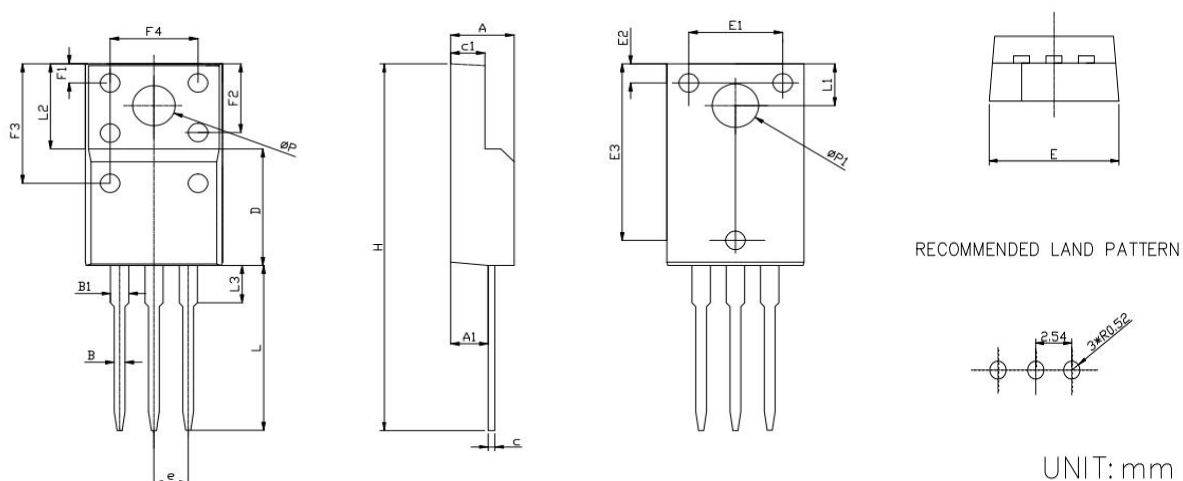
PWG15N65TFD

IGBT 650V, 1.55V, 15A



重庆平伟实业股份有限公司

Package Outline: TO-220TF-3L



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.50	4.90	0.177	0.193
A1	2.63	2.89	0.104	0.114
B	0.75	0.90	0.030	0.035
B1	1.15	1.55	0.045	0.061
C	0.40	0.60	0.016	0.024
C1	2.34	2.74	0.092	0.108
D	8.87	9.47	0.349	0.373
e	2.54		0.100	
E	9.86	10.46	0.388	0.412
E1	6.86	7.06	0.270	0.278
E2	1.40	1.60	0.055	
E3	13.80	14.00	0.543	0.551
F1	1.40	1.60	0.055	
F2	5.15	5.65	0.203	0.222
F3	9.10	9.70	0.358	0.382
F4	6.70	7.30	0.264	0.287
H	28.50	29.50	1.122	1.161
L	12.58	13.38	0.495	0.527
L1	3.15	3.45	0.124	0.136
L2	6.70		0.264	
L3	2.63	3.23	0.104	0.127
φP	2.90	3.48	0.114	0.137
φP1	3.15	3.75	0.124	0.148

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Buyer is responsible for its products and applications using PingWei products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by PingWei.

"Typical" parameters which may be provided in PingWei data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE